TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

HN3C01F

TV TUNER, VHF CONVERTER APPLICATION. TV VHF RF AMPLIFIER APPLICATION.

Including Two Devices in SM6 (Super Mini Type with 6Leads)

Low Reverse Transfer Capacitance : $C_{re} = 0.38pF$ (Typ.) High Transition Frequency : $f_T = 1400 MHz (Typ.)$

MAXIMUM RATINGS (Ta = 25° C) (Q₁, Q₂)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	30	V
Collector-Emitter Voltage	VCEO	20	V
Emitter-Base Voltage	V_{EBO}	3	V
Collector Current	$I_{\mathbf{C}}$	50	mA
Base Current	IB	25	mA
Collector Power Dissipation	PC*	300	mW
Junction Temperature	Tj	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

Total ELECTRICAL CHARACTERISTICS (Ta = 25°C) (Q₁, Q₂)

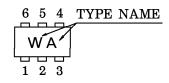
		Unit in mm	
	-	2.8 - 0.3 + 0.2 1.6 - 0.1 6 10 10 10 10 10 10 10 10 10 10	
	1.1 + 0.1	0.16 + 0.1	
1.	COLLECTOR 1	(C1) 5	
2.	COLLECTOR 1 EMITTER 1	(E1) ?	
3.	COLLECTOR 2	(C2)	
4.	EMITTER 2	(E2)	
5.	BASE 2	(B2)	
6.	BASE 1	(B1)	
JE	EDEC	_	
ΕĪ	AJ	_	
TC	OSHIBA 2	-3N1B	

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	$V_{CB} = 25V, I_{E} = 0$	_	_	0.1	μ A
Emitter Cut-off Current	IEBO	$V_{EB}=3V, I_{C}=0$	_	_	1.0	μ A
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	$I_{C}=1mA, I_{B}=0$	20	_	_	V
DC Current Gain	${ t h_{FE}}$	$V_{CE}=10V, I_{C}=5mA$	40	150	300	
Transition Frequency	$ m f_{T}$	$V_{ ext{CE}} = 10 \text{V}, I_{ ext{C}} = 5 \text{mA}, \\ f = 200 \text{MHz}$	900	1400	_	MHz
Reverse Transfer Capacitance Q ₁	C _{re (1)}	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	_	0.38	0.53	рF
Reverse Transfer Capacitance Q2	C _{re (2)}	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	_	0.31	0.46	рF
Collector-Base Time Constant Q ₁	C _c ·r _{bb} ' (1)	V_{CB} =10V, I_{C} =5mA, f =30MHz	_	6.0	12	ps
Collector-Base Time Constant Q2	C _c ·r _{bb} ' (2)	$egin{array}{l} V_{\mathrm{CB}} = 10\mathrm{V}, \ \mathrm{I_{\mathrm{C}}} = 5\mathrm{mA}, \\ \mathrm{f} = 30\mathrm{MHz} \end{array}$	_	5.5	11.5	ps

PIN ASSIGNMENT (TOP VIEW)

MARKING





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